



PATENT APPLICATION
Q-51885

17/Response
Kimura
9/3/02
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Akitaka KIMURA

Appln. No.: 09/161,981

Group Art Unit: 2812

Confirmation No.: 8269

Filed: September 29, 1998

Examiner: Mulpuri, S

For: SEMICONDUCTOR LAYER FORMED BY SELECTIVE DEPOSITION AND
METHOD FOR DEPOSITING SEMICONDUCTOR LAYER

REQUEST FOR RECONSIDERATION UNDER 37 C.F.R. § 1.111
AND
REQUEST FOR INTERVIEW

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the non-final Office Action (Paper No. 14) mailed February 26, 2002, Applicant respectfully traverses, and requests reconsideration and withdrawal of, the rejection of claims 1-4 and 9-17 under 35 U.S.C. § 103(a) as being unpatentable (obvious) over Admitted Prior Art (APA) in combination with Kamiyama '638 (**newly cited**). In particular, Applicant respectfully traverses the Examiner's conclusory statement that,

It would have been obvious to one of ordinary skill in the art to form silicon nitride in the invention of Admitted Prior Art because Kamiyama discloses forming functionally equivalent nitride mask as alternative to oxide mask to grow epitaxial layer.

More specifically, Applicant respectfully submits that the Examiner's APA/Kamiyama combination does not teach, or even remotely suggest, all of the features of the rejected claims, with each claim being taken as a **whole**.